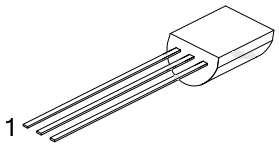
1.0A, 700V N-CHANNEL SUPER-JUNCTION MOSFET



TO-92

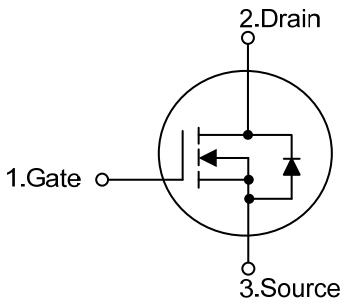
■ DESCRIPTION

The **UTC 1NM70-V** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at AC-DC converters for power applications.

■ FEATURES

* $R_{DS(on)} \leq 3.5\ \Omega$ @ V_{GS}=10V, I_D=0.5A
* Fast switching capability
* Avalanche energy specified
* Improved dv/dt capability, high ruggedness

■ SYMBOL



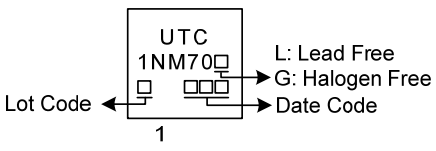
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
1NM70L-T92-B	1NM70G-T92-B	TO-92	G	D	S	Tape Box
1NM70L-T92-K	1NM70G-T92-K	TO-92	G	D	S	Bulk

Note: Pin Assignment: G: Gate D: Drain S: Source

1NM70G-T92-B (1)Packing Type (2)Package Type (3)Green Package	(1) B: Tape Box, K: Bulk (2) T92: TO-92 (3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	700	V
Gate-Source Voltage		V_{GSS}	±30	V
Continuous Drain Current		I_D	1	A
Pulsed Drain Current (Note 2)		I_{DM}	2	A
Avalanche Energy (Note 3)	Single Pulsed	E_{AS}	22	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.8	V/ns
Power Dissipation (T_A=25°C)		P_D	1.6	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L=138mH, I_{AS}=0.5A, V_{DD}=50V, R_G=25 Ω, Starting T_J = 25°C
4. I_{SD}≤1.0A, di/dt≤200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

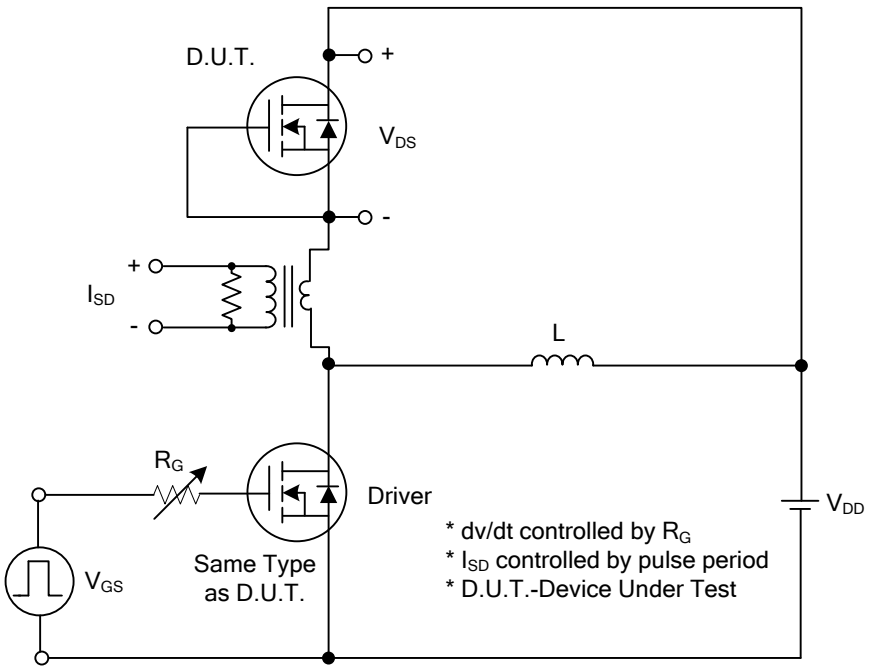
PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	180	°C/W
Junction to Case	θ_{JC}	75	°C/W

■ ELECTRICAL CHARACTERISTICS (T_C =25°C, unless otherwise specified)

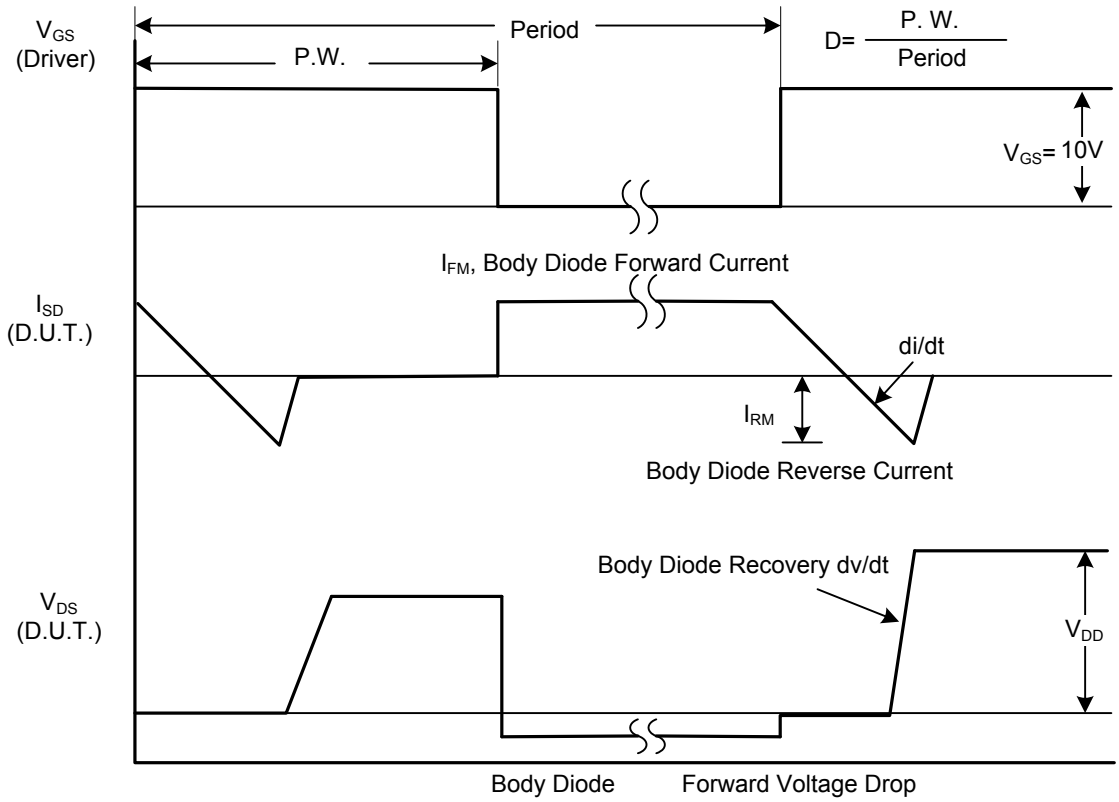
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS} = 0V, I_D = 250μA	700			V
Drain-Source Leakage Current		I_{DSS}	V_{DS} = 700V, V_{GS} = 0V			10	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS} = 30V, V_{DS} = 0V			100	nA
	Reverse		V_{GS} = -30V, V_{DS} = 0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS} = V_{GS}, I_D = 250μA	2.5		4.5	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS} = 10V, I_D =0.5A			3.5	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C_{ISS}	V_{DS} =25V, V_{GS} =0V, f =1MHz		124.7		pF
Output Capacitance		C_{OSS}			69.4		pF
Reverse Transfer Capacitance		C_{RSS}			6.2		pF
SWITCHING CHARACTERISTICS							
Total Gate Charge		Q_G	V_{DS}=560V, V_{GS}=10V, I_D=1A, I_G=1mA (Note 1, 2)		9.8		nC
Gate-Source Charge		Q_{GS}			2.8		nC
Gate-Drain Charge		Q_{GD}			1.5		nC
Turn-On Delay Time		$t_{D(ON)}$	V_{DD} =100V, V_{GS}=10V, I_D =1A, R_G=25Ω (Note 1, 2)		3.6		ns
Turn-On Rise Time		t_R			16.7		ns
Turn-Off Delay Time		$t_{D(OFF)}$			19		ns
Turn-Off Fall Time		t_F			38.3		ns
DRAIN-SOURCE DIODE CHARACTERISTICS							
Maximum Continuous Drain-Source Diode Forward Current		I_S				1	A
Maximum Pulsed Drain-Source Diode Forward Current		I_{SD}				2	A
Drain-Source Diode Forward Voltage		V_{SD}	I_S=1.0A, V_{GS}=0V			1.4	V
Reverse Recovery Time		t_{rr}	I_F=1.0A, V_{DD}=100V di/dt = 100A/μs		128		ns
Reverse Recovery Charge		Q_{rr}			0.6		μC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle≤2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

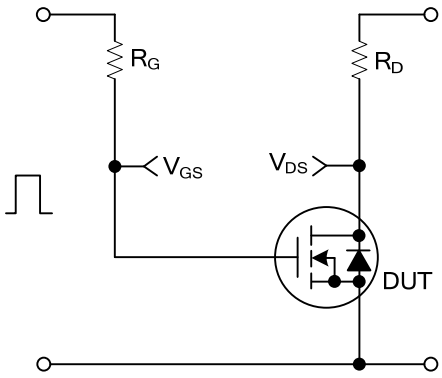


Peak Diode Recovery dv/dt Test Circuit



Peak Diode Recovery dv/dt Waveforms

■ TEST CIRCUITS AND WAVEFORMS



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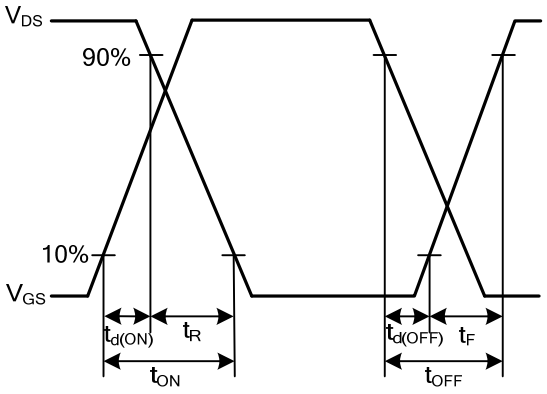
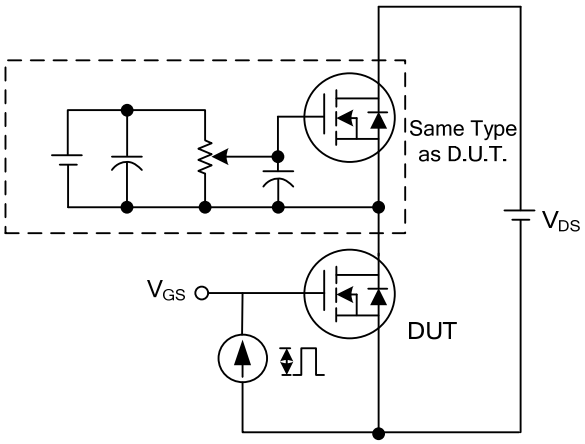
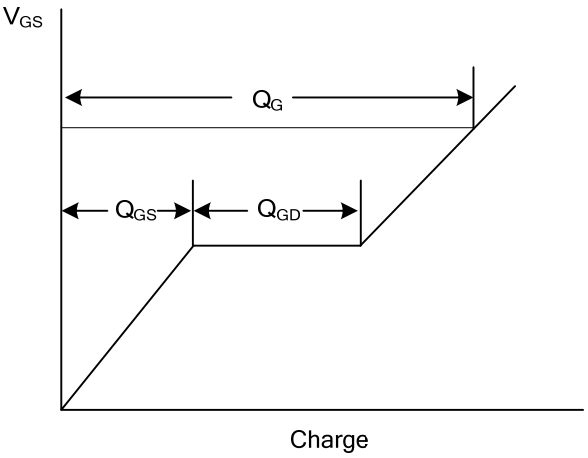


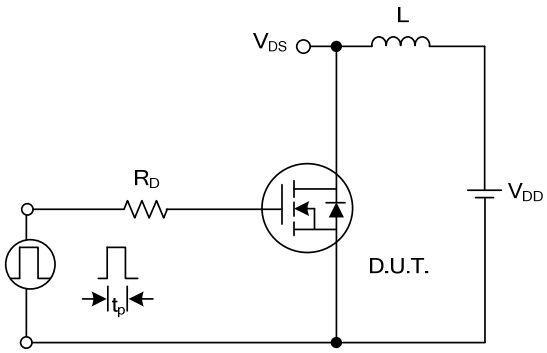
Switching Waveforms



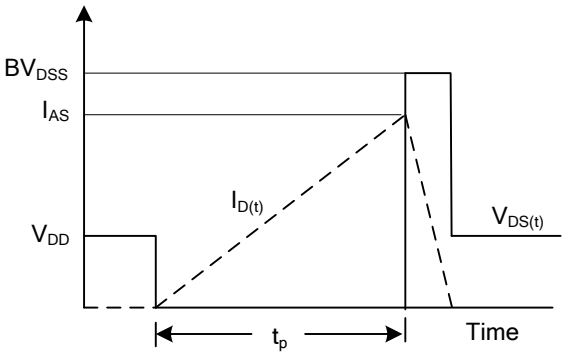
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms